

**Features :**

- > Isolated mounting base 3000V~
- > Pressure contact technology with Increased power cycling capability
- > Space and weight saving

**Typical Applications :**

- > Various rectifiers
- > DC supply for PWM inverter

V <sub>RSM</sub>	V <sub>RRM</sub>	品名
700V	600V	Mx110D60
900V	800V	Mx110D80
1100V	1000V	Mx110D100
1300V	1200V	Mx110D120
1500V	1400V	Mx110D140
1700V	1600V	Mx110D160
1900V	1800V	Mx110D180

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
I <sub>F(AV)</sub>	Mean forward current	180° half sine wave 50Hz Single side cooled, T <sub>C</sub> =100°C	150			110	A
I <sub>F(RMS)</sub>	RMS forward current					173	A
I <sub>RRM</sub>	Repetitive peak current	at V <sub>RRM</sub>	150			10	mA
I <sub>FSM</sub>	Surge forward current	V <sub>R</sub> =60%V <sub>RRM</sub> , t=10ms half sine,	150			2.6	kA
I <sup>2</sup> t	I <sup>2</sup> t for fusing coordination					33	10 <sup>3</sup> A <sup>2</sup> s
V <sub>FO</sub>	Threshold voltage		150			0.80	V
r <sub>F</sub>	Forward slope resistance					1.74	mΩ
V <sub>FM</sub>	Peak forward voltage	I <sub>FM</sub> =330A	25			1.45	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.27	°C/W
R <sub>th(c-h)</sub>	Thermal resistance case to heatsink	D.C. Single side cooled per chip				0.20	°C/W
V <sub>iso</sub>	Isolation voltage	50Hz,R.M.S,t=1min,I <sub>iso</sub> :1mA(MAX)		3000			V
F <sub>m</sub>	Terminal connection torque(M5)			2.5		4.0	N·m
	Mounting torque(M6)			4.5		6.0	N·m
T <sub>vj</sub>	Junction temperature			-40		150	°C
T <sub>stg</sub>	Stored temperature			-40		125	°C
W <sub>t</sub>	Weight				175		g
Outline	M01						

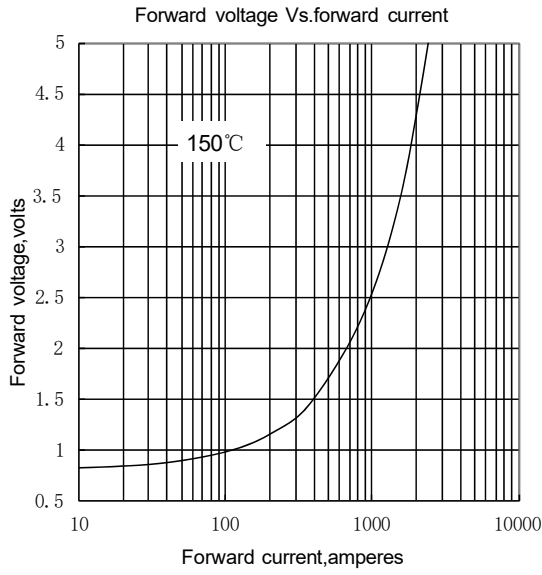


Fig.1

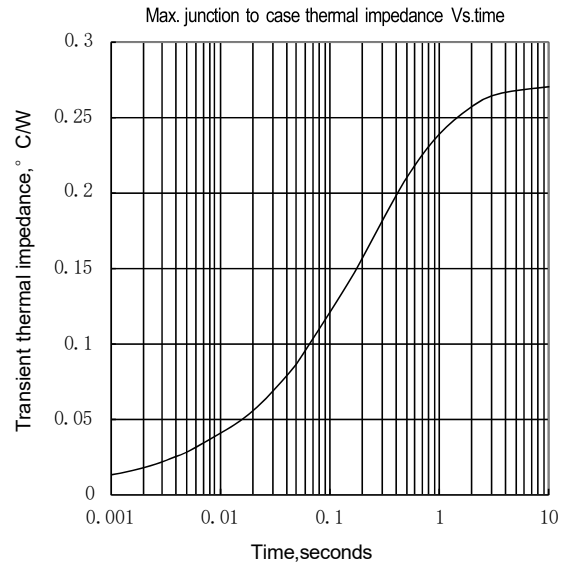


Fig.2

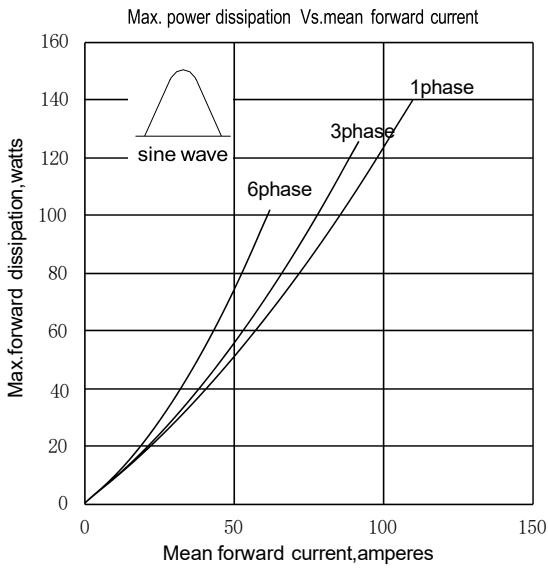


Fig.3

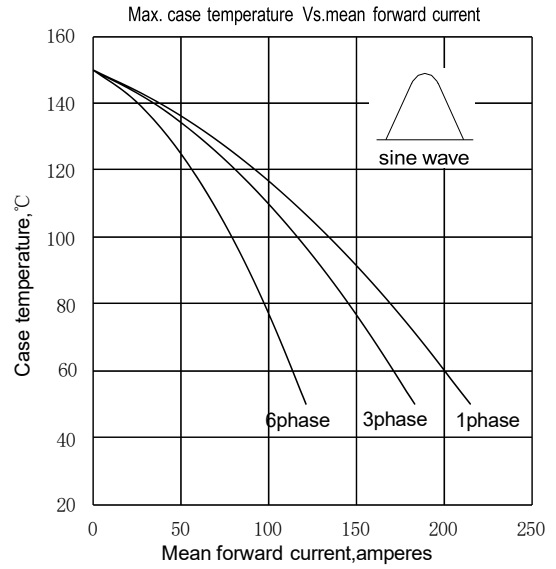


Fig.4

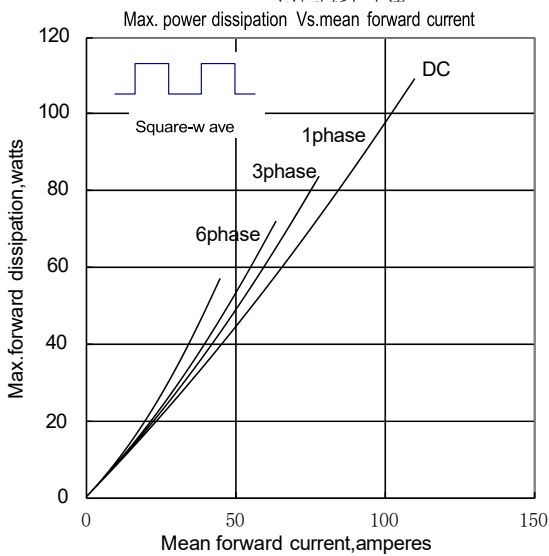


Fig.5

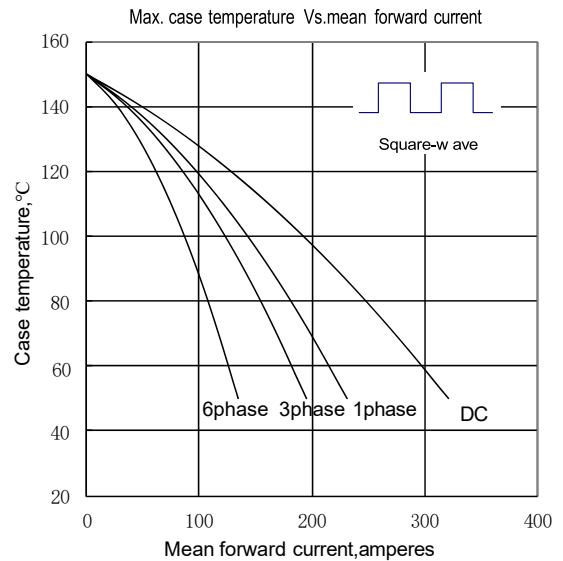


Fig.6

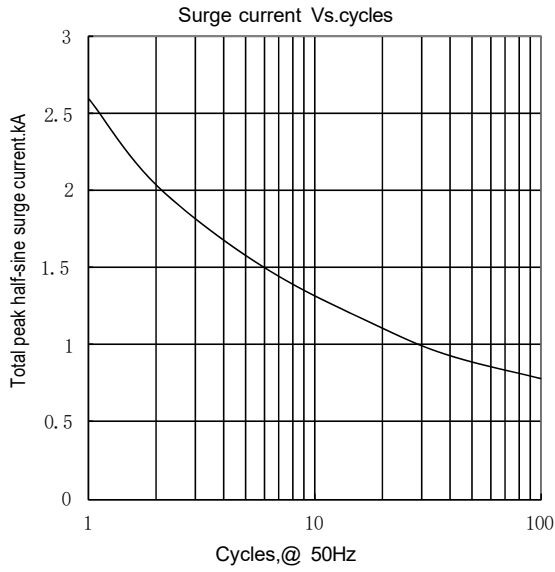
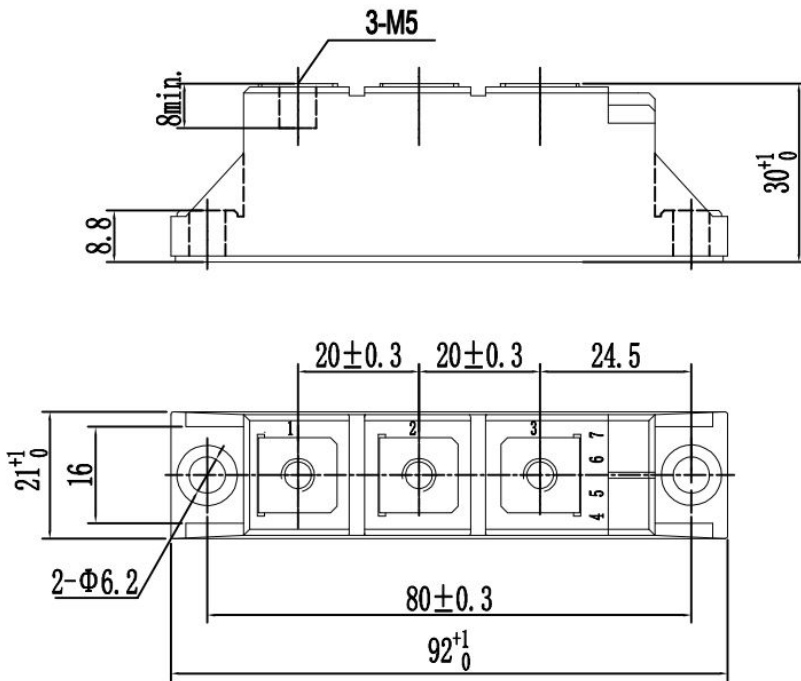


Fig.7

**Outline:**



Unmarked dimensional tolerance: ±0.5mm

